

SILICON POWER TRANSISTORS

Designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220V switchmode applications such as switching regulators, inverters, Motor controls, Solenoid/Relay drivers and deflection circuits.

DESCRIPTION :

- Collector-Emitter Sustaining Voltage
- VCEO(sus) = 400V(Min.)
- Collector Saturation Voltage
 VCE(sat) = 0.6(Max) @ IC= 2.0A

Minimum Lot-to-Lot variations for robust device performance and reliable operation

| MAXIMUM RATINGS | | | |
|---|------------------|-------------|-------|
| Characteristic | Symbol | MJE13005 | Unit |
| Collector-Emitter Voltage | V _{CEV} | 700 | V |
| Collector-Emitter Voltage | V _{CEO} | 400 | V |
| Emitter-Base Voltage | V _{EBO} | 9.0 | v |
| Collector Current-Continuous | lc | 4 | А |
| Collector Current-Peak | I _{CM} | 8 | А |
| Collector Power Dissipation $@T_a=25^\circ$ C | Pc | 2 | Watts |
| Collector Power Dissipation @T _C =25 $^\circ\!\!\!C$ | Pc | 75 | Watts |
| Junction Temperature | TJ | 150 | °C |
| Storage Temperature | T _{STG} | -65 to +150 | °C |

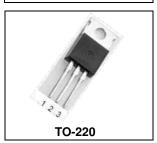
THERMAL CHARACTERISTICS

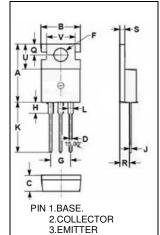
| Characteristic | Symbol | Max | Unit |
|---|---------------------|------|------|
| Thermal Resistance, Junction to Case | R _{th j-c} | 1.67 | °C/W |
| Thermal Resistance, Junction to Ambient | R _{th j-a} | 62.5 | °C/W |

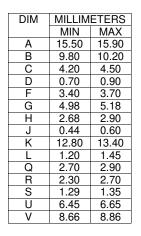
NPN

MJE13005

4 AMPERES SILICON POWER TRANSISTOR 400 VOLTS 75 WATTS







| Characteristic | Symbol | Min. | Max | Unit |
|--|-----------------------|---------|-------------------|------|
| OFFCHARACTERISTICS | | | | |
| Collector-Emitter Sustaining Voltage ($I_C = 10 \text{ mA}, I_B = 0$) | V _{CEO(SUS)} | 400 | | v |
| Collector Cutoff Current (V_{CEV} = 700 V, $V_{BE(off)}$ = 1.5V) | I _{CEV} | | 1.0 | mA |
| Emitter Cutoff Current (V_{EB} = 9.0 V, I_{C} = 0) | I _{EBO} | | 1.0 | mA |
| ON CHARACTERISTICS | | | | |
| $ DC Current Gain \\ (I_C = 1 A, V_{CE} = 5.0 V) \\ (I_C = 2 A, V_{CE} = 5.0 V) $ | h _{FE} | 10 8 | 60 40 | |
| Collector-Emitter Saturation Voltage ($I_C = 1.0 \text{ A}, I_B = 0.2 \text{ A}$) ($I_C = 2.0 \text{ A}, I_B = 0.5 \text{ A}$) ($I_C = 4.0 \text{ A}, I_B = 1.0 \text{ A}$) | V _{CE(sat)} | | 0.5 0.6 1.0 | v |
| Base-Emitter Saturation Voltage ($I_C = 1 A$, $I_B = 0.2 A$) ($I_C = 2 A$, $I_B = 0.5 A$) | V _{BE(sat)} | | 1.2 1.6 | v |

| Current gain-Bandwidth product $(I_C=0.5 \text{ A}, V_{CE} = 10 \text{ V})$ | f⊤ | 4 | | MHz |
|---|----|---|--|-----|
|---|----|---|--|-----|



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